AMENDMENTS TO THE CLAIMS

1 - 4 (Cancelled).

5. (Currently Amended) A production method for a laminated type positive temperature-resistance semiconductor ceramic element comprising

providing a mixture comprising a barium compound, a titanium compound and a nickel compound, wherein the nickel compound is present in the mixture in a positive amount up to about 0.2 mol%,

calcining the mixture to obtain a calcined product;

forming a ceramic green sheet comprising the calcined product;

applying a conductive paste for forming an internal electrode layer of the laminated type semiconductor ceramic element on the ceramic green sheet;

laminating the ceramic green sheet so as to provide a laminated product; and

baking the laminated product under a reducing atmosphere and reoxidizing the baked laminate so as to form a laminated positive temperature-resistance semiconductor ceramic ~~elemen~~ element.

6. (Previously Presented) The production method of claim 5 wherein the mixture calcined contains a boron compound.

7. (Currently amended) ~~The~~ A production method ~~of claim 6~~ for a laminated type positive temperature-resistance semiconductor ceramic element comprising

providing a mixture comprising a barium compound, a titanium compound, a boron compound and a nickel compound, wherein the boron compound is about 0.2 to 20 mol% and the nickel compound is present in the mixture in a positive amount up to about 0.2 mol%,

calcining the mixture to obtain a calcined product;

forming a ceramic green sheet comprising the calcined product;

applying a conductive paste for forming an internal electrode layer of the laminated type semiconductor ceramic element on the ceramic green sheet;

laminating the ceramic green sheet so as to provide a laminated product; and

baking the laminated product under a reducing atmosphere and reoxidizing the baked laminate so as to form a laminated positive temperature-resistance semiconductor ceramic element.

8. (Canceled)

9. (Previously Presented) The production method of claim [[8]] 7 in which an external electrode electrically conducted to the internal electrode is formed on the laminated semiconductor ceramic element.

10. (Cancelled).

11. (Previously Presented) The production method according to claim 9 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

12. (Previously Presented) The production method according to claim 11 wherein the conductive paste contains nickel.

13. (Previously Presented) The production method according to claim 12 comprising forming the mixture of the barium compound, titanium compound and nickel compound.

14 – 16. (Canceled)

17. (Currently amended) The production method according to claim ~~15~~ 20 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

18. (Previously Presented) The production method according to claim 17 wherein the conductive paste contains nickel.

19. (Previously Presented) The production method according to claim 18 comprising forming the mixture of the barium compound, titanium compound and nickel compound.

20. (Previously Presented) The production method of claim 5 in which an external electrode electrically conducted to the internal electrode is formed on the laminated semiconductor ceramic element.

21. (Cancelled).

22. (Previously Presented) The production method according to claim 5 wherein the laminated product is baked at a temperature of 900 to 1300°C for 0.5 to 5 hours.

23. (Previously Presented) The production method according to claim 5 wherein the conductive paste contains nickel.

24. (Previously Presented) The production method according to claim 5 comprising forming the mixture of the barium compound, titanium compound and nickel compound.